2N6547

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Switchmode Serier NPN Silicon Power Transistor 15 AMPERES, 300 and 400 VOLTS, 175 WATTS



2N6546 2N6547

TO-3

FEATURES:

The 2N6547 transistor is designed for high-voltage, high-speed, power switching in inductive circuits where fall time is critical. They are particularly suited for 115 and 220 volt line operated switch-mode applications

Specification Features -

High Temperature Performance Specified for:

Reversed Biased SOA with Inductive Loads

Switching Times with Inductive Loads

Saturation Voltages

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Leakage Currents

APPLICATIONS:

- 1. Switching Regulators
- 2. PWM Inverters and Motor Controls
- 3. Solenoid and Relay Drivers
- 4. Deflection Circuits







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ABSOLUTE MAXIMUM RATINGS (T_a = 25 °C)

Rating	Symbol	Value	Unit			
Collector-Emitter Voltage	V _{CEO(sus)}	400	Vdc			
Collector-Emitter Voltage	V _{CEX(sus)}	450	Vdc			
Collector-Emitter Voltage	VCEV	850	Vdc			
Emitter Base Voltage	VEB	9.0	Vdc			
Collector Current — Continuous — Peak (2)	IC ICM	15 30	Adc			
Base Current — Continuous — Peak (2)	IB IBM	10 20	Adc			
Emitter Current — Continuous — Peak (2)	IЕ IЕМ	25 35	Adc			
Total Power Dissipation @ T _C = 25°C @ T _C = 100°C Derate above 25°C	PD	175 100 1.0	Watts W/°C			
Operating and Storage Junction Temperature Range	TJ, T _{stg}	-65 to +200	°C			
THERMAL CHARACTERISTICS						
Characteristic	Symbol	Max	Unit			
Thermal Resistance, Junction to Case	R JC	1.0	°C/W			
Maximum Lead Temperature for Soldering Purposes: 1/8 from Case for 5 Seconds	ΤL	275	°C			





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ELECTRICAL CHARACTERISTICS (T_A=25 ° C unless otherwise specified)

	Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS	(1)			6		
Collector-Emitter Sustain (IC = 100 mA, IB = 0)	ing Voltage	2N6546 2N6547	VCEO(sus)	300 400		Vdc
Collector-Emitter Sustain (IC = 8.0 A, V _{clamp} = R (IC = 15 A, V _{clamp} = R T _C = 100°C)	ing Voltage Rated V _{CEX} , T _C = 100°C) ated V _{CEO} = 100 V,	2N6546 2N6547 2N6546 2N6547	VCEX(sus)	350 450 200 300		Vdc
Collector Cutoff Current (VCEV = Rated Value, V (VCEV = Rated Value, V	VBE(off) = 1.5 Vdc) VBE(off) = 1.5 Vdc, T _C = 100°C)		ICEV		1.0 4.0	mAdc
Collector Cutoff Current (VCE = Rated VCEV. R	BE = 50 , TC = 100°C)		ICER	-	5.0	mAdc
Emitter Cutoff Current (VEB = 9.0 Vdc, IC = 0)	1		IEBO	-	1.0	mAdc
SECOND BREAKDOWN						
Second Breakdown Collect t = 1.0 s (non-repetitive	ctor Current with base forward biased) (V _{CE} = 100 Vdc)		IS/b	0.2	-	Adc
ON CHARACTERISTICS (1)					
DC Current Gain (I _C = 5.0 Adc, V _{CE} = 2. (I _C = 10 Adc, V _{CE} = 2.0	0 Vdc) 0 Vdc)		hFE	1 2 6.0	60 30	-
Collector-Emitter Saturati (I _C = 10 Adc, I _B = 2.0 A (I _C = 15 Adc, I _B = 3.0 A (I _C = 10 Adc, I _B = 2.0 A	ion Voltage vdc) vdc, T _C = 100°C}		VCE(sat)	111	1.5 5.0 2.5	Vdc
Base-Emitter Saturation A (I _C = 10 Adc, I _B = 2.0 A (I _C = 10 Adc, I _B = 2.0 A	voltage vdc) vdc, T _C = 100°C		VBE(sat)	11	1.6 1.6	Vdc
DYNAMIC CHARACTERIS	TICS					
Current-Gain — Bandwid (IC = 500 mAdc, VCE =	th Product 10 Vdc, f _{test} = 1.0 MHz)		fT	6.0	28	MHz
Output Capacitance (V _{CB} = 10 Vdc, I _E = 0,	f _{test} = 1.0 MHz)		Cob	125	500	pF
SWITCHING CHARACTER	RISTICS					1
Resistive Load						0
Delay Time			ta	-	0.05	s
Rise Time	(V _{CC} = 250 V, I _C = 10 A,		ţr	—	1.0	s
Storage Time	IB1 = IB2 = 2.0 A, tp = 100 s, Duty Cycle ≤ 2.0%)		ts	—	4.0	S
Fall Time	r musel star province to a single para 1999		^t f	-	0.7	\$
Inductive Load, Clamped		00			i i	
Storage Time	(IC = 10 A(pk), Vclamp = Rated VCEX, IB1	= 2.0 A,	ts	-	5.0	\$
Fall Time	V _{BE(off)} = 5.0 Vdc, T _C = 100°C)		tf		1.5	S
		21		Тур	lical	
Storage Time	(I _C = 10 A(pk), V _{clamp} = Rated V _{CEX} , I _{B1} = 2.0 A, V _{BE(off)} = 5.0 Vdc, T _C = 25°C)		ts	2.0		s
Fall Time			tf	0.09		s

(1) Pulse Test: Pulse Width = 300 s, Duty Cycle = 2%.

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Continental Device India Pvt. Limited An IATF 16949, ISO9001 and ISO 14001 Certified Company **TYPICAL CHARACTERISTICS CURVES** 100 V_{CE}, COLLECTOR-EMITTER VOLTAGE (VOLTS) 2.0 70 TJ = 150YC 1.6 50 hFE, DC CURRENT GAIN 25)C IC = 2.0 A 30 1.2 20 0.8 -55YC 10 +++ 0.4 VCE = 2.0 V 7.0 V_{CE} = 10 V 5.0 L 0.2 11 0.07 0.1 0.3 0.5 1.0 2.0 3.0 5.0 7.0 10 20 IC, COLLECTOR CURRENT (AMP)







Figure 2. Collector Saturation Region



Figure 4. Temperature Coefficients



Figure 6. Turn-Off Time

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t, TIME (ns) 300

200

100

70

50

30 0.02

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td @ VBE(off) = 5.0 V

0.1 0.2 0.5

IC, COLLECTOR CURRENT (AMP)

Figure 5. Turn-On Time

1.0 2.0 5.0 10 20

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0.05











50 20 1.0 ms COLLECTOR CURRENT (AMP) 10 5.0 ms 5.0 100 S dc 2.0 1.0 0.5 TC = 25YC 0.2 BONDING WIRE LIMITED 0.1 0.05 THERMAL LIMIT (SINGLE PULSE) SECOND BREAKDOWN LIMIT <u>ن</u> 0.02 2N6546 CURVES APPLY BELOW RATED VCEO 0.01 2N6547 0.005 5.0 7.0 10 20 30 50 70 100 200 300 400 VCE, COLLECTOR-EMITTER VOLTAGE (VOLTS)

TYPICAL CHARACTERISTICS CURVES

Figure 7. Forward Bias Safe Operating Area







Figure 8. Reverse Bias Safe Operating Area



Figure 10. Thermal Response

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Package Details





DIM	MIN.	MAX.
А		39.37
В	1	22.22
С	6.35	8.50
D	0.96	1.09
Е		1.77
F	29.90	30.40
G	10.69	11.18
Н	5.20	5.72
J	16.64	17.15
K	11.15	12.25
L	_	26.67
М	3.84	4.19

All dimensions in mm.



PIN CONFIGURATION

- 1. BASE
- 2. EMITTER
- 3. COLLECTOR

Packing Detail

PACKAGE	STANDARD PACK		INNER CARTON BOX		OUTER CARTON BOX		
	Details	Net Weight/Qty	Size	Qty	Size	Qty	Gr Wt
TO-3	100 pcs/pkt	1.3 kg/100 pcs	12.5" x 8" x 1.8"	0.1K	17" x 11.5" x 21"	2K	27.5 kgs

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Recommended Product Storage Environment for Discrete Semiconductor Devices

This storage environment assumes that the Diodes and transistors are packed properly inside the original packing supplied by CDIL.

- · Temperature 5 °C to 30 °C
- · Humidity between 40 to 70 %RH
- · Air should be clean.
- · Avoid harmful gas or dust.
- \cdot Avoid outdoor exposure or storage in areas subject to rain or water spraying .
- · Avoid storage in areas subject to corrosive gas or dust. Product shall not be stored in areas exposed to direct sunlight.
- · Avoid rapid change of temperature.
- · Avoid condensation.
- $\cdot\,$ Mechanical stress such as vibration and impact shall be avoided.
- $\cdot\,$ The product shall not be placed directly on the floor.
- The product shall be stored on a plane area. They should not be turned upside down. They should not be placed against the wall.

Shelf Life of CDIL Products

The shelf life of products is the period from product manufacture to shipment to customers. The product can be unconditionally shipped within this period. The period is defined as 2 years.

If products are stored longer than the shelf life of 2 years the products shall be subjected to quality check as per CDIL quality procedure.

The products are further warranted for another one year after the date of shipment subject to the above conditions in CDIL original packing.

Floor Life of CDIL Products and MSL Level

When the products are opened from the original packing, the floor life will start.

For this, the following JEDEC table may be referred:

JEDEC MSL Level				
Level	Time	Condition		
1	Unlimited	≤30 °C / 85% RH		
2	1 Year	≤30 °C / 60% RH		
2a	4 Weeks	≤30 °C / 60% RH		
3	168 Hours	≤30 °C / 60% RH		
4	72 Hours	≤30 °C / 60% RH		
5	48 Hours	≤30 °C / 60% RH		
5a	24 Hours	≤30 °C / 60% RH		
6	Time on Label(TOL)	≤30 °C / 60% RH		



Customer Notes

Component Disposal Instructions

- 1. CDIL Semiconductor Devices are RoHS compliant, customers are requested to please dispose as per prevailing Environmental Legislation of their Country.
- 2. In Europe, please dispose as per EU Directive 2002/96/EC on Waste Electrical and Electronic Equipment (WEEE).

Disclaimer

The product information and the selection guides facilitate selection of the CDIL's Semiconductor Device(s) best suited for application in your product(s) as per your requirement. It is recommended that you completely review our Data Sheet(s) so as to confirm that the Device(s) meet functionality parameters for your application. The information furnished in the Data Sheet and on the CDIL Web Site/CD are believed to be accurate and reliable. CDIL however, does not assume responsibility for inaccuracies or incomplete information. Furthermore, CDIL does not assume liability whatsoever, arising out of the application or use of any CDIL product; neither does it convey any license under its patent rights nor rights of others. These products are not designed for use in life saving/support appliances or systems. CDIL customers selling these products (either as individual Semiconductor Devices or incorporated in their end products), in any life saving/support appliances or systems or applications do so at their own risk and CDIL will not be responsible for any damages resulting from such sale(s).

CDIL strives for continuous improvement and reserves the right to change the specifications of its products without prior notice.



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